

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Attorney Docket No.: VISH-8728

Inventor(s): Deva N. Pattanayak and Robert Xu

Serial No.: Group Art Unit:

Filed: 12/02/03 Examiner:

Title: CLOSED CELL TRENCH METAL-OXIDE-SEMICONDUCTOR FIELD EFFECT TRANSISTOR

Commissioner of Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Sir:

Information Disclosure Statement Submitted Pursuant to 37 C.F.R. 1.97(b)

The citations referenced herein, copies attached, may be material to the examination of the above-identified application and are, therefore, submitted in compliance with the duty of disclosure as defined in 37 C.F.R. 1.56. The Examiner is requested to make these citations of official record in the application.

This Information Disclosure Statement submitted in accordance with 37 C.F.R. 1.97(b) is not to be construed as a representation that a search has been made, that additional items material to the examination of this application do not exist, or that any one or more of these citations constitute prior art under 35 U.S.C. 102.

The Examiner's attention is respectfully directed to the following U.S. Patents:

<u>Pat. No.</u>	<u>Pat. Title</u>	<u>Grant Date</u>
5,929,481	HIGH DENSITY TRENCH DMOS TRANSISTOR WITH TRENCH BOTTOM IMPLANT	07/27/99

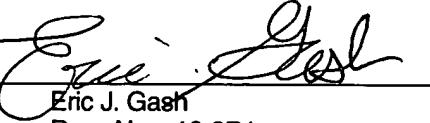
Please direct all correspondence concerning the above-identified application to the following address:

WAGNER, MURABITO & HAO LLP
Two North Market Street, Third Floor
San Jose, California 95113
(408) 938-9060

Respectfully submitted,

Date: December 7, 2003

By:


Eric J. Gash
Reg. No. 46,274

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Patent Application

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EFFECT TRANSISTORForm 1449**U.S. Patent Documents**

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
A	5,929,481	07/27/99		Hshieh, et al.	257	328	11/04/97
B							
C							
D							
E							
F							
G							
H							
I							
J							
K							

Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation
							Yes
							No
L							
M							
N							
O							
P							
Q							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	R	
	S	
	T	
Examiner		Date Considered

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered.
 Include copy of this form with next communication to applicant.